# P-Channel 80-V (D-S) MOSFET

## **Key Features:**

- Low r<sub>DS(on)</sub> trench technology
- · Low thermal impedance
- · Fast switching speed

### **Typical Applications:**

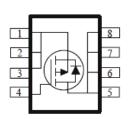
- White LED boost converters
- Automotive Systems
- Industrial DC/DC Conversion Circuits

PRODUCT SUMMARY			
V <sub>DS</sub> (V)	$r_{DS(on)}(m\Omega)$	I <sub>D</sub> (A)	
-80	129 @ V <sub>GS</sub> = -10V	-4.3	
-60	149 @ V <sub>GS</sub> = -4.5V	-4	



**FREE** 





ABSOLUTE MAXIMUM RATINGS ( $T_A = 25^{\circ}$ C UNLESS OTHERWISE NOTED)							
Parameter	Symbol	Limit	Units				
Drain-Source Voltage	$V_{DS}$	-80	V				
Gate-Source Voltage		$V_{GS}$	±20	V			
Continuous Drain Current a	T <sub>A</sub> =25°C	l <sub>D</sub>	-4.3				
Continuous Drain Current	T <sub>A</sub> =70°C		-3	Α			
Pulsed Drain Current <sup>b</sup>		I <sub>DM</sub> -20					
Continuous Source Current (Diode Conduction) a		I <sub>S</sub>	-4.4	Α			
Power Dissipation <sup>a</sup>	T <sub>A</sub> =25°C	$P_{D}$	3.5	W			
Power Dissipation	T <sub>A</sub> =70°C	' D	2	V V			
Operating Junction and Storage Temperature Range		$T_J,T_stg$	-55 to 150	°C			

THERMAL RESISTANCE RATINGS							
Parameter			Maximum	Units			
Maximum Junction-to-Ambient <sup>a</sup>	t <= 10 sec	$R_{\theta JA}$	35	°C/W			
IMAXIIIIUIII JUIICUOII-to-AIIIDIEIIt	Steady State	· νθJΑ	81	C/VV			

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#### Notes

- a. Surface Mounted on 1" x 1" FR4 Board.
- b. Pulse width limited by maximum junction temperature

### **Electrical Characteristics**

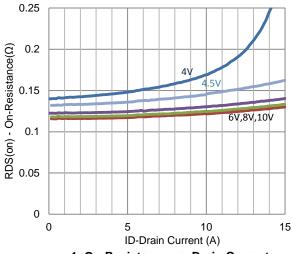
Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit		
Static								
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_{D} = -250 \text{ uA}$	-1			V		
Gate-Body Leakage	I <sub>GSS</sub>	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			±100	nA		
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	$V_{DS} = -64 \text{ V}, V_{GS} = 0 \text{ V}$			-1	uA		
Zero Gate Voltage Brain Garrent	1088	$V_{DS} = -64 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55^{\circ}\text{C}$			-5	uA		
On-State Drain Current	$I_{D(on)}$	$V_{DS} = -5 \text{ V}, V_{GS} = -10 \text{ V}$	-2.1			Α		
Drain-Source On-Resistance	r	$V_{GS} = -10 \text{ V}, I_{D} = -3.4 \text{ A}$		129		mΩ		
Drain-Source On-Resistance	r <sub>DS(on)</sub>	$V_{GS} = -4.5 \text{ V}, I_D = -3.3 \text{ A}$			149	11152		
Forward Transconductance	g <sub>fs</sub>	$V_{DS} = -15 \text{ V}, I_{D} = -10 \text{ A}$		10		S		
Diode Forward Voltage	$V_{SD}$	$I_{S} = -2 \text{ A}, V_{GS} = 0 \text{ V}$		0.79		V		
		Dynamic						
Total Gate Charge	$Q_g$	$V_{DS} = -40 \text{ V}, V_{GS} = -4.5 \text{ V},$		13				
Gate-Source Charge	$Q_{gs}$	$I_{D} = -3.4 \text{ A}$		5.6		nC		
Gate-Drain Charge	$Q_{gd}$	1 <sub>D</sub> = 0.4 A		6.1				
Turn-On Delay Time	t <sub>d(on)</sub>	$V_{DS} = -40 \text{ V}, R_{L} = 11.6 \Omega,$		9				
Rise Time	t <sub>r</sub>	$I_{DS} = -40 \text{ V}, \text{ KL} = 11.0 \Omega,$ $I_{D} = -3.4 \text{ A},$		9		nc		
Turn-Off Delay Time	t <sub>d(off)</sub>	$V_{GEN} = -10 \text{ V}, R_{GEN} = 6 \Omega$		79		ns		
Fall Time	$t_f$	V GEN - 10 V, 11 GEN - 0 12		48				
Input Capacitance	C <sub>iss</sub>			1230				
Output Capacitance	C <sub>oss</sub>	$V_{DS} = -15 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$		141		pF		
Reverse Transfer Capacitance	C <sub>rss</sub>			72				

#### Notes

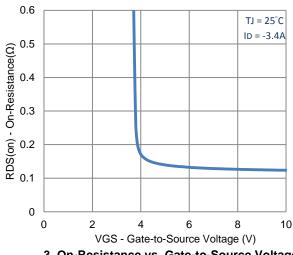
- a. Pulse test: PW <= 300us duty cycle <= 2%.
- b. Guaranteed by design, not subject to production testing.

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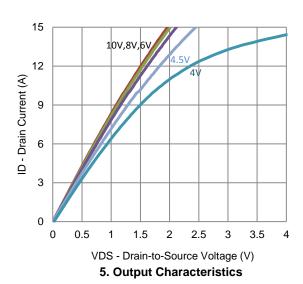
## **Typical Electrical Characteristics**



1. On-Resistance vs. Drain Current

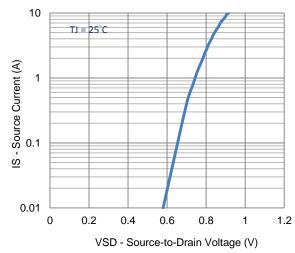


3. On-Resistance vs. Gate-to-Source Voltage

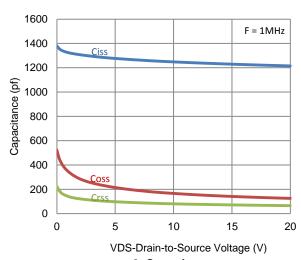


10  $TJ = 25^{\circ}$ ¢ 9 8 ID - Drain Current (A) 5 4 3 2 1 0 3 0 2 4 5 VGS - Gate-to-Source Voltage (V)

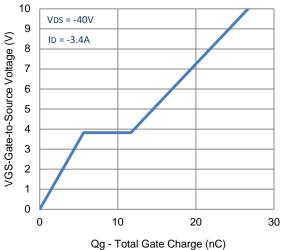
2. Transfer Characteristics



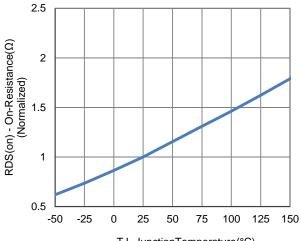
4. Drain-to-Source Forward Voltage



## **Typical Electrical Characteristics**

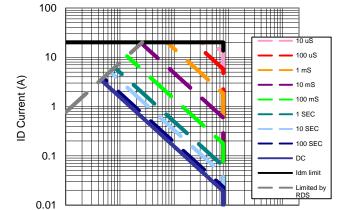


7. Gate Charge



TJ -JunctionTemperature(°C)

8. Normalized On-Resistance Vs



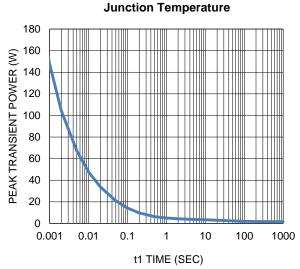
VDS Drain to Source Voltage (V)

9. Safe Operating Area

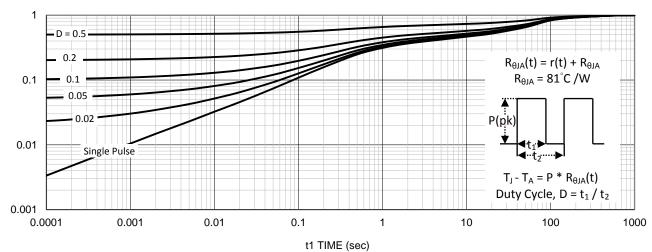
100

1000

10



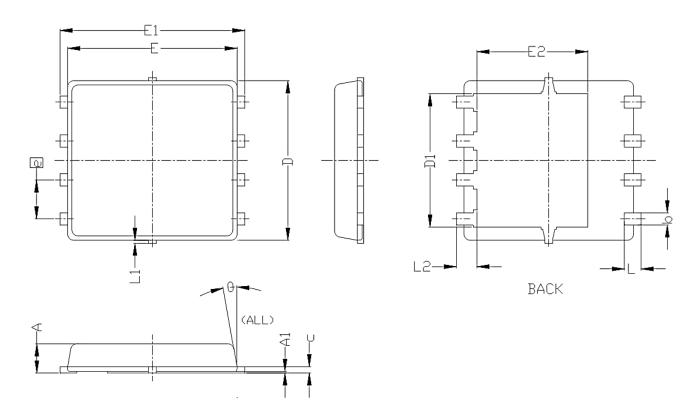
10. Single Pulse Maximum Power Dissipation



11. Normalized Thermal Transient Junction to Ambient

0.1

# Package Information



SYMBOLS	DIMENSIONS IN MILLIMETERS			DIMENSIONS IN INCHES			
STMBOLS	MIN	NOM	MAX	MIN	NOM	MAX	
Α	0.85	0.95	1.00	0.033	0.037	0.039	
A1	0.00		0.05	0.000		0.002	
b	0.30	0.40	0.50	0.012	0.016	0.020	
С	0. 15	0. 20	0. 25	0.006	0.008	0.010	
D		5. 20 BSC			0. 205 BSC		
D1	4. 35 BSC			0. 171 BSC			
E	5, 55 BSC			0, 219 BSC			
E1	6. 05 BSC			0. 238 BSC			
E2	3. 62 BSC			0. 143 BSC			
e	1. 27 BSC			0. 050 BSC			
L	0.45	0.55	0.65	0.018	0.022	0.026	
L1	0		0. 15	0		0.006	
L2	0.68 REF			0.027 REF			
θ	0°		10°	0°		10°	